

NTMFS4C022N

Power MOSFET

30 V, 2.1 mΩ, 136 A, Single N-Channel, SO-8FL

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit | |
|--|--|--------------------------|------------------|---|
| Drain-to-Source Voltage | V_{DSS} | 30 | V | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3) | Steady State | $T_C = 25^\circ\text{C}$ | I_D 136 | A |
| | | $T_C = 25^\circ\text{C}$ | P_D 64 | W |
| Power Dissipation $R_{\theta JC}$ (Notes 1, 3) | Steady State | $T_A = 25^\circ\text{C}$ | I_D 30 | A |
| | | $T_A = 25^\circ\text{C}$ | P_D 3.1 | W |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3) | | | | |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2, 3) | Steady State | $T_A = 25^\circ\text{C}$ | I_D 30 | A |
| | | $T_A = 25^\circ\text{C}$ | P_D 3.1 | W |
| Pulsed Drain Current | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | I_{DM} 352 | A | |
| Operating Junction and Storage Temperature | T_J, T_{stg} | -55 to 150 | $^\circ\text{C}$ | |
| Source Current (Body Diode) | I_S | 53 | A | |
| Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 11 \text{ A}$) | E_{AS} | 549 | mJ | |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|---------------------------|
| Junction-to-Case – Steady State (Note 2) | $R_{\theta JC}$ | 1.95 | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 40 | |

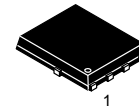
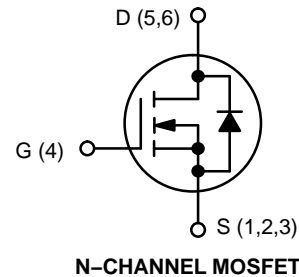
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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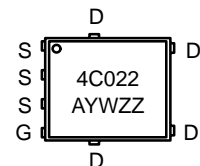
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| $V_{(BR)DSS}$ | $R_{DS(on)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 30 V | 1.7 mΩ @ 10 V | 136 A |
| | 2.4 mΩ @ 4.5 V | |



SO-8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

ORDERING INFORMATION

| Device | Package | Shipping† |
|----------------|---------------------|-----------------------|
| NTMFS4C022NT1G | SO-8FL (Pb-Free) | 1500 / Tape & Reel |
| NTMFS4C022NT3G | SO-8FL (Pb-Free) | 5000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTMFS4C022N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|--------------------------------------|--|------------------------|------|-----|-------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0 V, I _D = 250 μA | 30 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(BR)DSS} /T _J | | | 18.2 | | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V, V _{DS} = 24 V | T _J = 25 °C | | 1 | μA |
| | | | T _J = 125°C | | 10 | |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = 20 V | | | 100 | nA |

ON CHARACTERISTICS (Note 4)

| | | | | | | |
|--|-------------------------------------|---|-----------------------|-----|-----|-------|
| Gate Threshold Voltage | V _{GS(TH)} | V _{GS} = V _{DS} , I _D = 250 μA | 1.3 | | 2.2 | V |
| Negative Threshold Temperature Coefficient | V _{GS(TH)} /T _J | | | 4.8 | | mV/°C |
| Drain-to-Source On Resistance | R _{DS(on)} | V _{GS} = 10 V | I _D = 30 A | 1.4 | 1.7 | mΩ |
| | | V _{GS} = 4.5 V | I _D = 30 A | 2.0 | 2.4 | |
| Forward Transconductance | g _{FS} | V _{DS} = 3 V, I _D = 30 A | | 136 | | S |
| Gate Resistance | R _G | T _A = 25 °C | | 1.0 | | Ω |

CHARGES AND CAPACITANCES

| | | | | | | |
|------------------------------|---------------------|--|--|------|--|----|
| Input Capacitance | C _{ISS} | V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V | | 3071 | | pF |
| Output Capacitance | C _{OSS} | | | 1673 | | |
| Reverse Transfer Capacitance | C _{RSS} | | | 67 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 30 A | | 20.8 | | nC |
| Threshold Gate Charge | Q _{G(TH)} | | | 4.9 | | |
| Gate-to-Source Charge | Q _{GS} | | | 8.5 | | |
| Gate-to-Drain Charge | Q _{GD} | | | 4.7 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 10 V, V _{DS} = 15 V, I _D = 30 A | | 45.2 | | nC |

SWITCHING CHARACTERISTICS (Note 5)

| | | | | | | |
|---------------------|---------------------|---|--|----|--|----|
| Turn-On Delay Time | t _{d(ON)} | V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 15 A, R _G = 3.0 Ω | | 14 | | ns |
| Rise Time | t _r | | | 32 | | |
| Turn-Off Delay Time | t _{d(OFF)} | | | 27 | | |
| Fall Time | t _f | | | 17 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | |
|-------------------------|-----------------|---|------------------------|------|-----|----|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V, I _S = 10 A | T _J = 25°C | 0.75 | 1.1 | V |
| | | | T _J = 125°C | 0.6 | | |
| Reverse Recovery Time | t _{RR} | V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A | | 47 | | ns |
| Charge Time | t _a | | | 23 | | |
| Discharge Time | t _b | | | 24 | | |
| Reverse Recovery Charge | Q _{RR} | | | 39 | | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

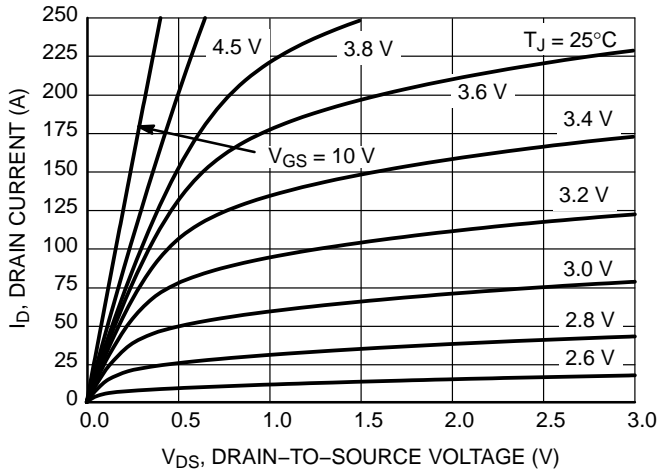


Figure 1. On-Region Characteristics

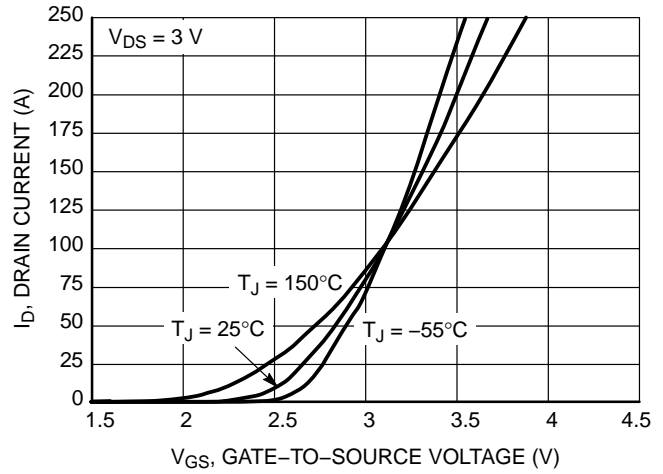


Figure 2. Transfer Characteristics

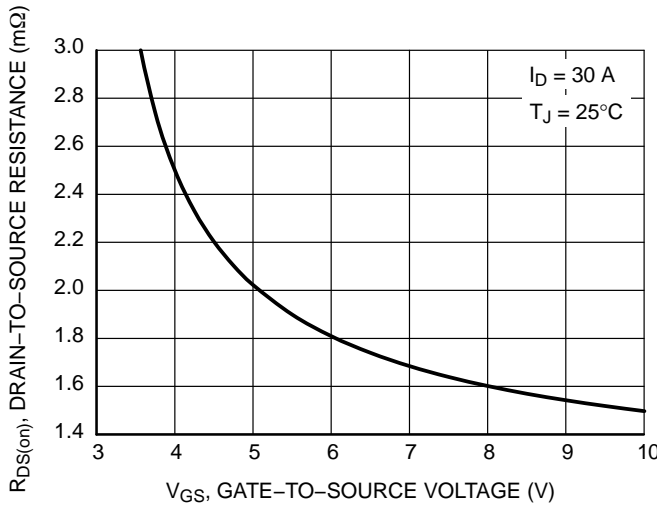


Figure 3. On-Resistance vs. V_{GS}

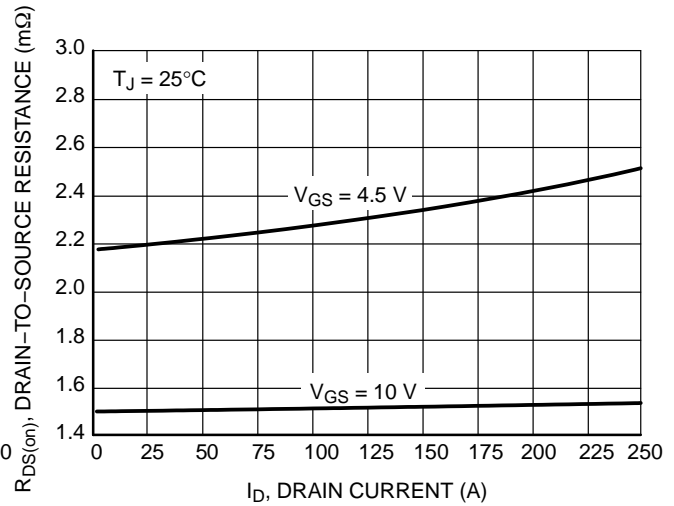


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

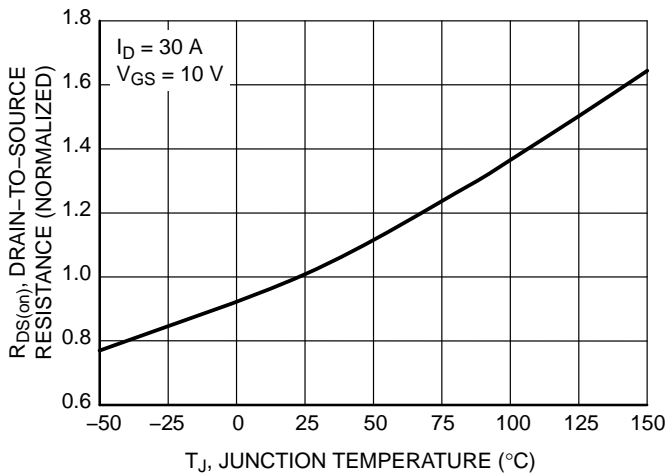


Figure 5. On-Resistance Variation with Temperature

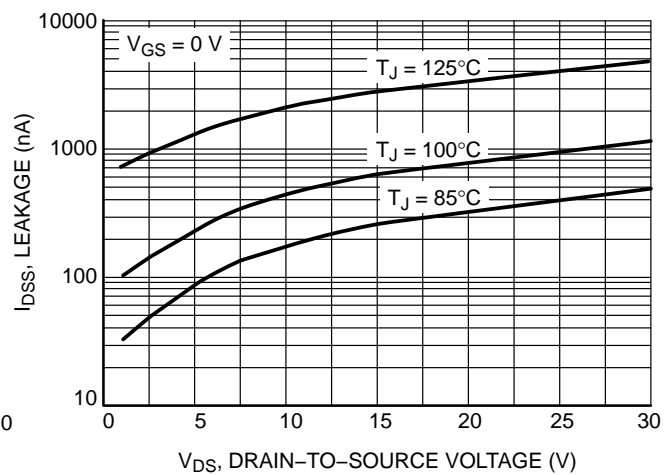


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

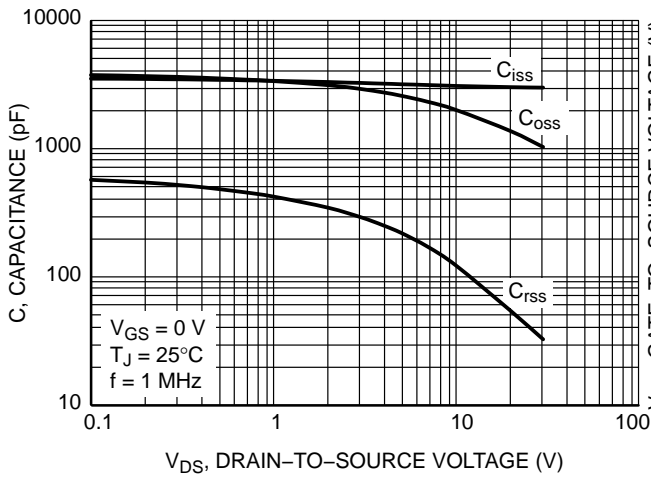


Figure 7. Capacitance Variation

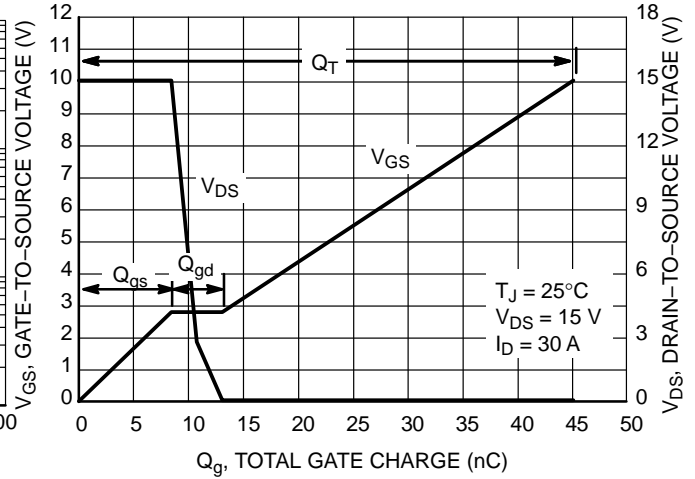


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

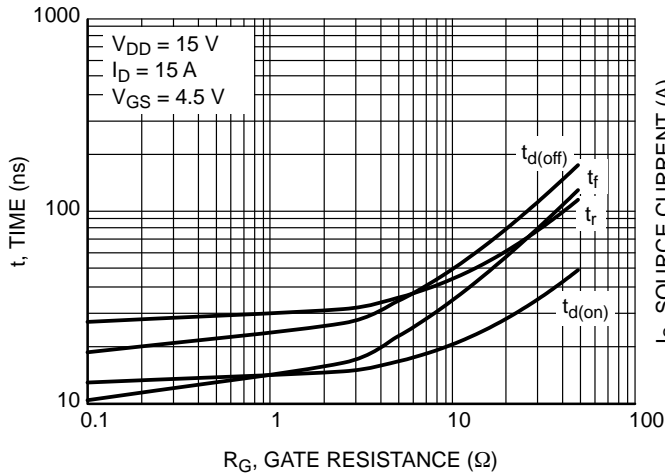


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

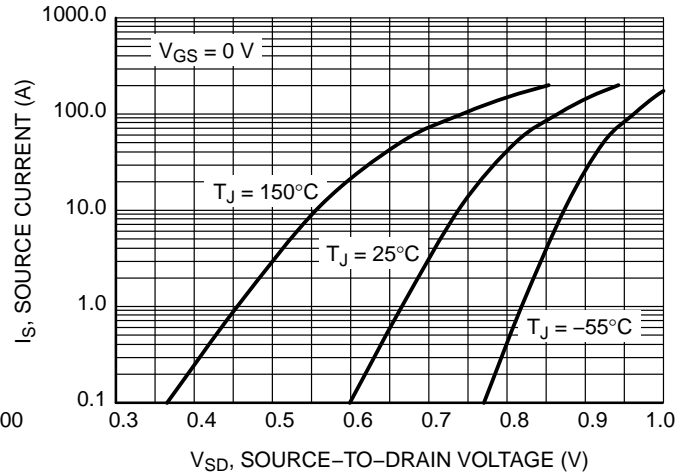


Figure 10. Diode Forward Voltage vs. Current

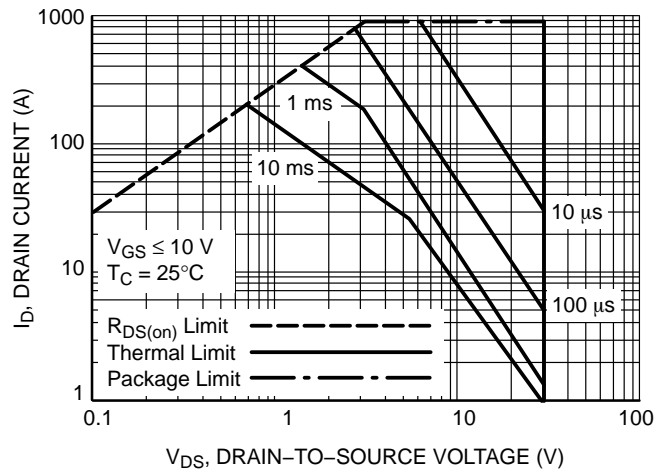


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS

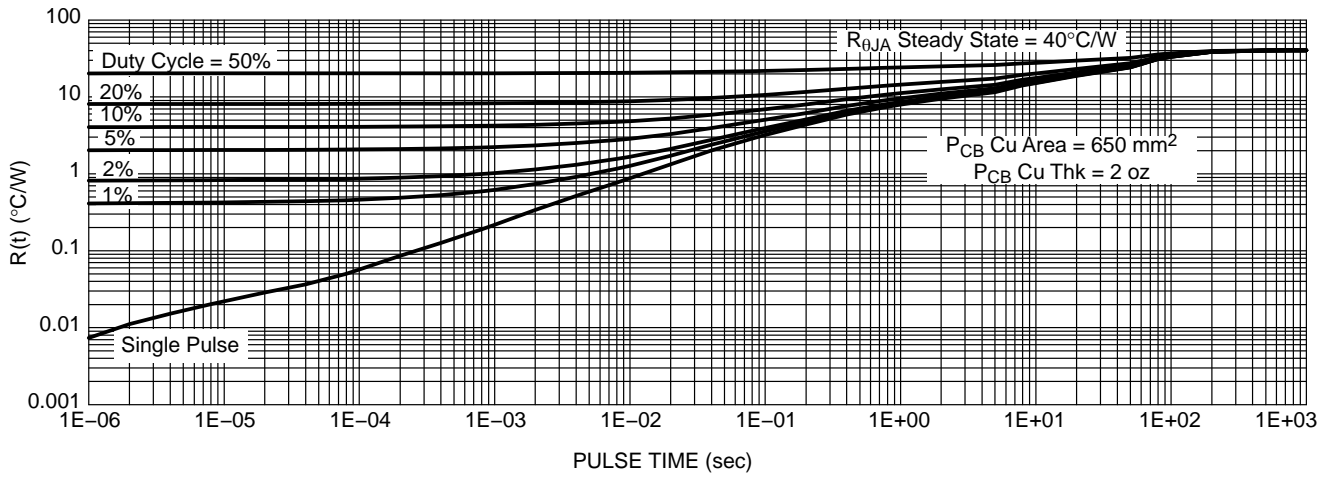


Figure 12. Thermal Impedance (Junction-to-Ambient)

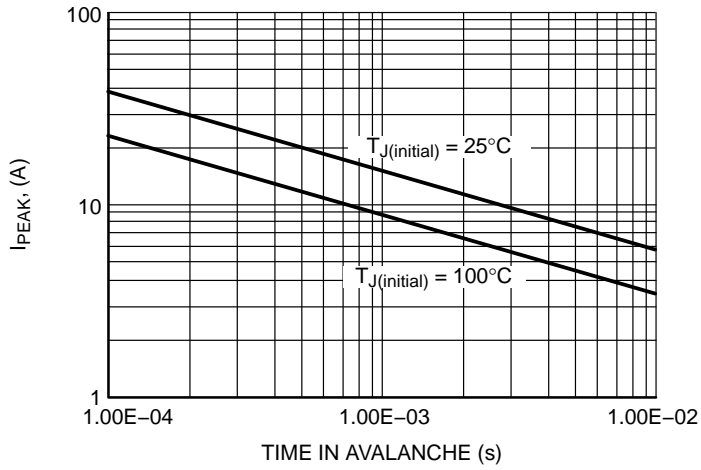


Figure 13. Avalanche Characteristics

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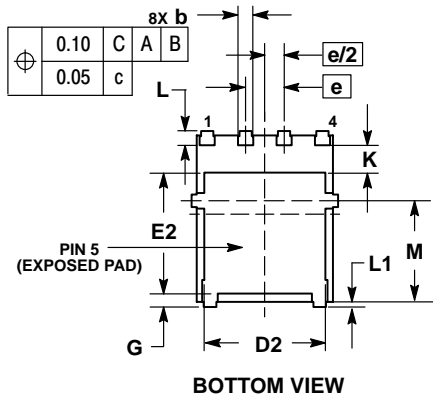
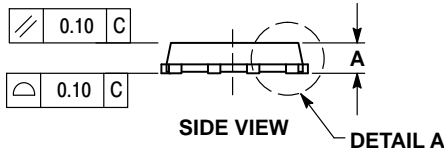
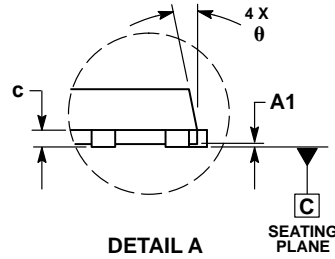
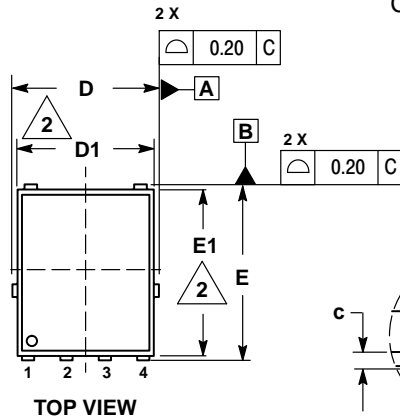
PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

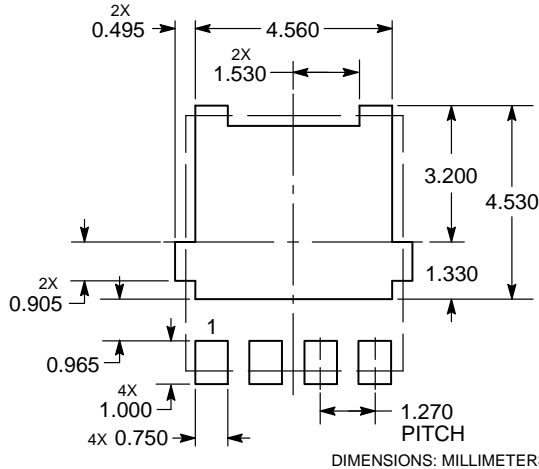
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| MILLIMETERS | | | |
|-------------|-----------|-------|------|
| DIM | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | --- | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | 5.00 | 5.15 | 5.30 |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.80 | 4.00 | 4.20 |
| E | 6.00 | 6.15 | 6.30 |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.45 | 3.65 | 3.85 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.575 | 0.71 |
| K | 1.20 | 1.35 | 1.50 |
| L | 0.51 | 0.575 | 0.71 |
| L1 | 0.125 REF | | |
| M | 3.00 | 3.40 | 3.80 |
| θ | 0 ° | --- | 12 ° |



RECOMMENDED SOLDERING FOOTPRINT*



STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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